

Electrical Features

- Low V_{CEsat}
- Low Switching Losses
- V_{CEsat} with positive Temperature Coefficient
- High Short Circuit Capability, Self Limiting Short Circuit Current



Typical Applications

- Motor Drives
- Auxiliary Inverters

Mechanical Features

- Copper Base Plate
- Standard Housing

IGBT, Inverter

Maximum Rated Values							
Symbol	Item	Conditions	Rating	Unit			
IGBT							
V_{CES}	Collector-emitter voltage	$T_{vj}=25^{\circ}C$	1700	V			
V_{GES}	Gate-emitter voltage	-	± 20	V			
I_C	Collector current,DC	$T_C=100^{\circ}C, T_{vj}=175^{\circ}C$	50	A			
I_{CRM}	Repetitive peak collector current	$t_p=1ms$	100	A			
P_{tot}	Total power dissipation	$T_C=25^{\circ}C, T_{vj}=175^{\circ}C$	-	W			
Characteristics Values							
Symbol	Item	Conditions	Values			Unit	
IGBT			Min.	Typ.	Max.		
I_{CES}	Collector-emitter cut-off current	$V_{CE}=1700V, V_{GE}=0V, T_{vj}=25^{\circ}C$	-	-	1	mA	
I_{GES}	Gate leakage current	$V_{CE}=0V, V_{GE}=20V, T_{vj}=25^{\circ}C$	-	-	100	nA	
$V_{GE(th)}$	Gate-emitter threshold voltage	$I_C=1mA, V_{CE}=V_{GE}, T_{vj}=25^{\circ}C$	5.2	5.8	6.6	V	
V_{CEsat}	Collector-emitter saturation voltage	$I_C=50A$ $V_{GE}=15V$	$T_{vj}=25^{\circ}C$	-	1.55		2.40
			$T_{vj}=125^{\circ}C$	-	1.81		-
			$T_{vj}=150^{\circ}C$	-	1.84	-	
C_{ies}	Input capacitance	$V_{CE}=25V, V_{GE}=0V$ $f=1MHz, T_{vj}=25^{\circ}C$	-	7.9	-	nF	
C_{oes}	Output capacitance		-	1.5	-		
C_{res}	Reverse transfer capacitance		-	1.3	-		
Q_G	Gate charge	$V_{GE}=-15...+15V$	-	0.45	-	μC	
R_g	Internal gate resistance	$T_{vj}=25^{\circ}C$	-	-	-	Ω	
$t_{d(on)}$	Turn-on delay time		$T_{vj}=25^{\circ}C$	-	189.9	-	ns
			$T_{vj}=125^{\circ}C$	-	198.1	-	
			$T_{vj}=150^{\circ}C$	-	199.2	-	
t_r	Rise time		$T_{vj}=25^{\circ}C$	-	67.5	-	
			$T_{vj}=125^{\circ}C$	-	85.1	-	
			$T_{vj}=150^{\circ}C$	-	86.3	-	

$t_{d(off)}$	Turn-off delay time	$V_{CC}=900V$ $I_C=50A$ $V_{GE}=\pm 15V$	$T_{vj}=25^{\circ}C$	-	381.3	-	
			$T_{vj}=125^{\circ}C$	-	425.5	-	
			$T_{vj}=150^{\circ}C$	-	473.9	-	
t_f	Fall time	$R_{G(on)}=15\Omega$ $R_{G(off)}=15\Omega$ $di/dt=1034A/\mu s$ $du/dt=5607V/\mu s$	$T_{vj}=25^{\circ}C$	-	582.9	-	
			$T_{vj}=125^{\circ}C$	-	767.1	-	
			$T_{vj}=150^{\circ}C$	-	985.1	-	
E_{on}	Turn-on energy (per pulse)	$(T_{vj}=150^{\circ}C)$	$T_{vj}=25^{\circ}C$	-	15.9	-	mJ
			$T_{vj}=125^{\circ}C$	-	21.2	-	
			$T_{vj}=150^{\circ}C$	-	21.4	-	
E_{off}	Turn-off energy (per pulse)	$T_{vj}=25^{\circ}C$	-	12.8	-		
		$T_{vj}=125^{\circ}C$	-	15.9	-		
		$T_{vj}=150^{\circ}C$	-	17.6	-		
SC data	Short-circuit current	$V_{CC}=900V, V_{GE}\leq 15V$ $V_{CES}\leq 1700V, t_p\leq 10\mu s$	$T_{vj}=25^{\circ}C$	-	318	-	A
			$T_{vj}=150^{\circ}C$	-	271	-	
R_{thJC}	Thermal resistance, junction to case	Per IGBT	-	-	-	-	K/W
R_{thCH}	Thermal resistance, case to heatsink	Per IGBT $\lambda_{grease}=1W/(m\cdot K)$	-	-	-	-	K/W
T_{vjop}	Temperature under switching conditions		-40	-	150		$^{\circ}C$

**Diode, Inverter
Maximum Rated Values**

Symbol	Item	Conditions	Rating	Unit	
V_{RRM}	Repetitive peak reverse voltage	$T_{vj}=25^{\circ}C$	1700	V	
I_F	Forward current, DC		50	A	
I_{FRM}	Repetitive peak forward current	$t_p=1ms$	100	A	
I^2t	I^2t -value	$V_R=0V, t_p=10ms$	$T_{vj}=25^{\circ}C$	-	A^2s
		$V_R=0V, t_p=10ms$	$T_{vj}=150^{\circ}C$	-	

Characteristic Values

			Min.	Typ.	Max.		
V_F	Continuous forward voltage	$I_F=50A$ $V_{GE}=0V$	$T_{vj}=25^{\circ}C$	-	1.28	-	V
			$T_{vj}=125^{\circ}C$	-	1.33	-	
			$T_{vj}=150^{\circ}C$	-	1.41	-	
I_{RM}	Peak reverse recovery current		$T_{vj}=25^{\circ}C$	-	51.0	-	A
			$T_{vj}=125^{\circ}C$	-	55.0	-	
			$T_{vj}=150^{\circ}C$	-	56.0	-	
t_{rr}	Reverse recovery time	$V_R=900V$ $I_F=50A$ $V_{GE}=-15V$	$T_{vj}=25^{\circ}C$	-	709.8	-	ns
			$T_{vj}=125^{\circ}C$	-	983.0	-	
			$T_{vj}=150^{\circ}C$	-	1017	-	
Q_r	Recovered charge	$-di_F/dt=698A/\mu s$ $(T_{vj}=150^{\circ}C)$	$T_{vj}=25^{\circ}C$	-	16.8	-	μC
			$T_{vj}=125^{\circ}C$	-	26.7	-	
			$T_{vj}=150^{\circ}C$	-	28.1	-	

E _{rec}	Reverse recovery energy	V _R =900V	T _{vj} =25°C	-	10.0	-	mJ	
		I _F =50A	T _{vj} =125°C	-	16.5	-		
		V _{GE} =-15V	T _{vj} =150°C	-	17.4	-		
R _{thJC}	Thermal resistance, junction to case	Per diode			-	-	-	K/W
R _{thCH}	Thermal resistance, case to heatsink	Per diode, λ _{grease} =1 W/(mK)			-	-	-	K/W
T _{vjop}	Temperature under switching conditions				-40	-	150	°C

NTC Thermistor Characteristics

Symbol	Item	Conditions	Values			Unit
			Min.	Typ.	Max.	
R ₂₅	Rated resistance	T _C =25°C	-	5	-	kΩ
ΔR/R	Deviation of resistance	T _C =100°C, R ₁₀₀ =493Ω	-5	-	5	%
P ₂₅	Power dissipation	T _C =25°C	-	-	20	mW
B _{25/50}	B-constant	R ₂ =R ₂₅ exp[B _{25/50} (1/T ₂ -1/(298.15K))]	-	3375	-	K
B _{25/80}	B-constant	R ₂ =R ₂₅ exp[B _{25/80} (1/T ₂ -1/(298.15K))]	-	3411	-	
B _{25/100}	B-constant	R ₂ =R ₂₅ exp[B _{25/100} (1/T ₂ -1/(298.15K))]	-	3433	-	

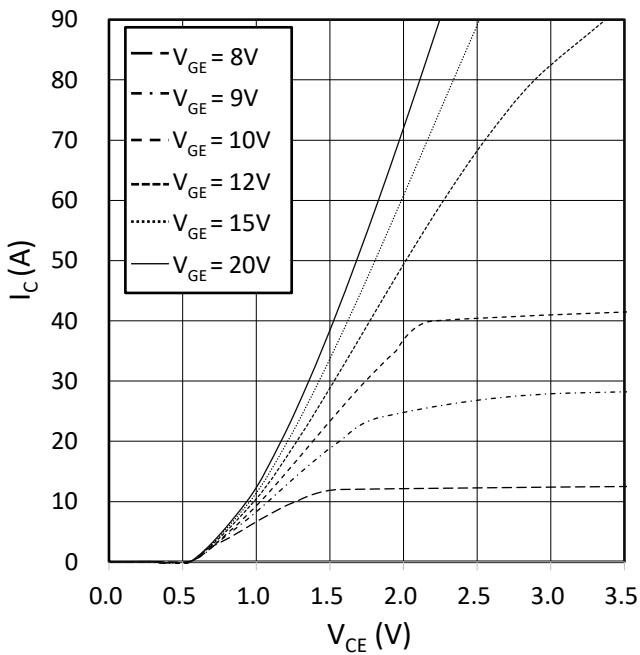
Module

Symbol	Item	Conditions	Rating			Unit
V _{ISOL}	Isolation voltage	Terminals to baseplate, RMS, f=50Hz, t=1min	4000			V
-	Material of module baseplate	-	Cu			
-	Internal isolation	Basic insulation (class 1, IEC 61140)	Al ₂ O ₃			
CTI	Comperative tracking index	-	>200			
T _{vj max}	Maximum junction temperature	-	175			°C
T _{vj op}	Operating junction temperature	Continuous operationg(under switching)	-40~150			°C
T _{stg}	Storage temperature	-	-40~125			°C
Symbol	Item	Conditions	Values			Unit
			Min.	Typ.	Max.	
M _s	Mounting torque	Mounting to heat sink, M5 screw	3	-	6	Nm
RCC'+EE'		TC = 25°C, per switch	-	2.53	-	mΩ
L _{sCE}	Stray inductance module		-	43	-	nH
ds	Creepage distance	Terminal to terminal	-	-	-	mm
		Terminal to base plate	-	10	-	
da	Clearance	Terminal to terminal	-	-	-	mm
		Terminal to base plate	-	7.5	-	
m	Weight	-	-	175	-	g

output characteristic IGBT, Inverter (typical)

$I_C = f(V_{CE})$

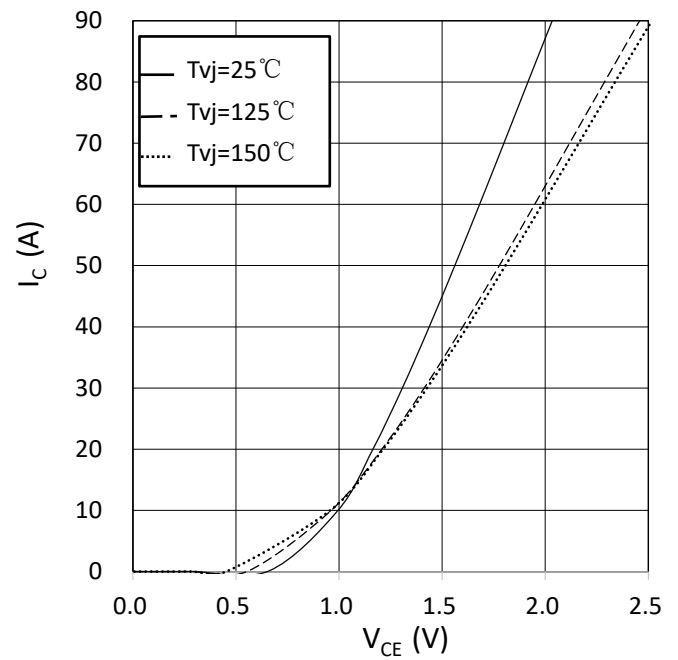
$T_{vj} = 150^\circ\text{C}$



output characteristic IGBT, Inverter (typical)

$I_C = f(V_{CE})$

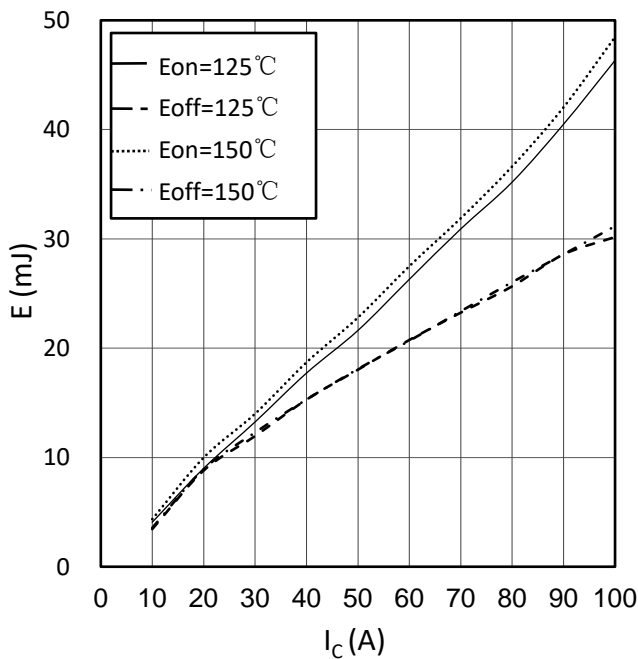
$V_{GE} = 15\text{ V}$



switching losses IGBT, Inverter (typical)

$E_{on} = f(I_C), E_{off} = f(I_C)$

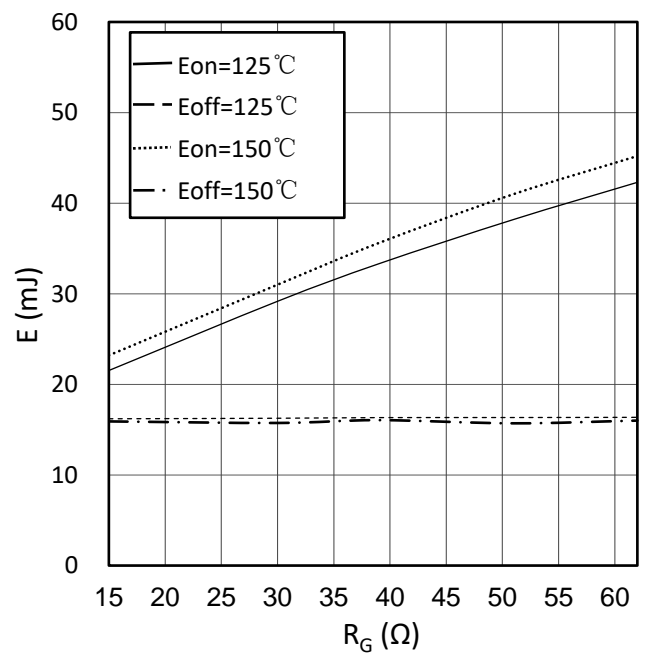
$V_{GE} = \pm 15\text{V}, R_{Gon} = 15\Omega, R_{Goff} = 15\Omega, V_{CE} = 900\text{V}$



switching losses IGBT, Inverter (typical)

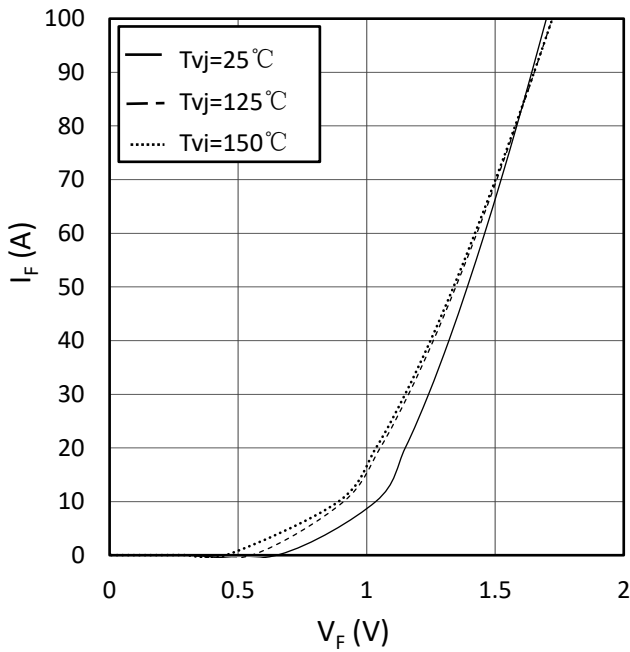
$E_{on} = f(R_G), E_{off} = f(R_G)$

$V_{GE} = \pm 15\text{V}, I_C = 50\text{A}, V_{CE} = 900\text{V}$



forward characteristic of Diode, Inverter (typical)

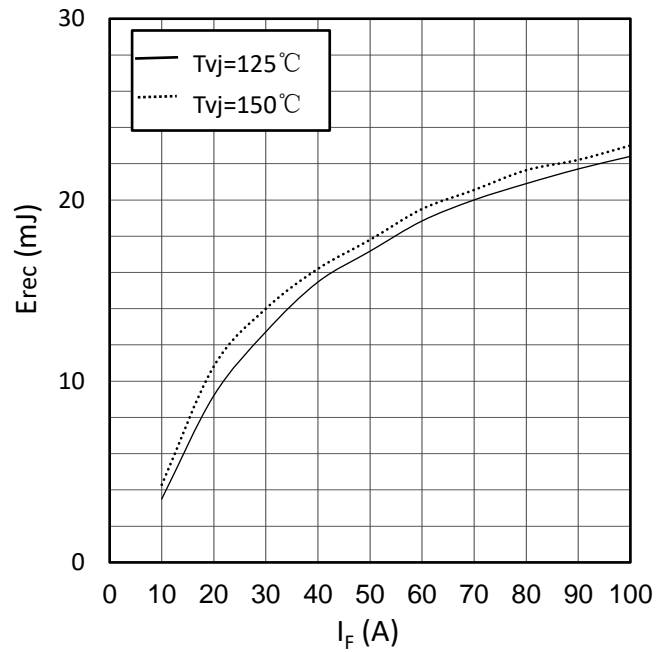
$I_F = f(V_F)$



switching losses Diode, Inverter (typical)

$E_{rec} = f(I_F)$

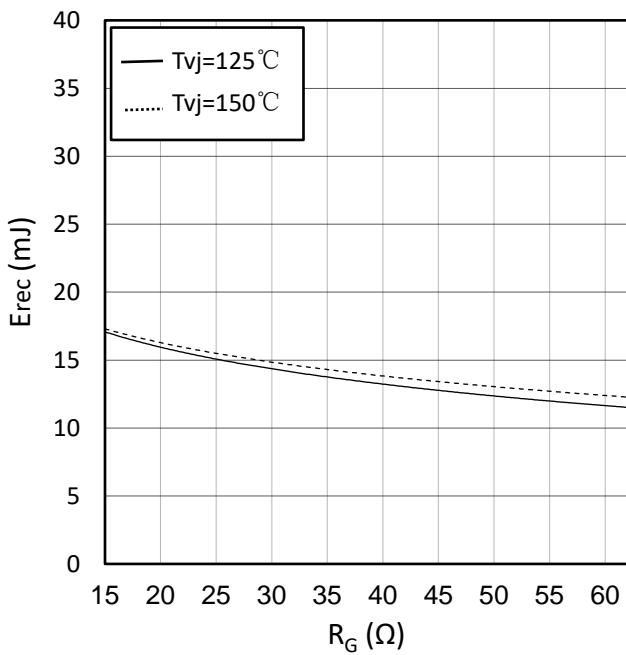
$R_{Gon}=15\Omega, V_{CE}=900\text{V}$



switching losses Diode, Inverter (typical)

$E_{rec} = f(R_G)$

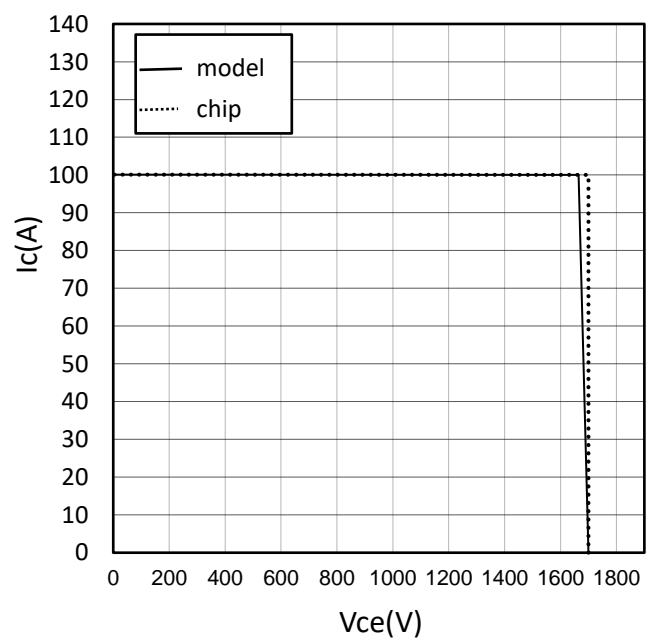
$I_F=50\text{A}, V_{CE}=900\text{V}$



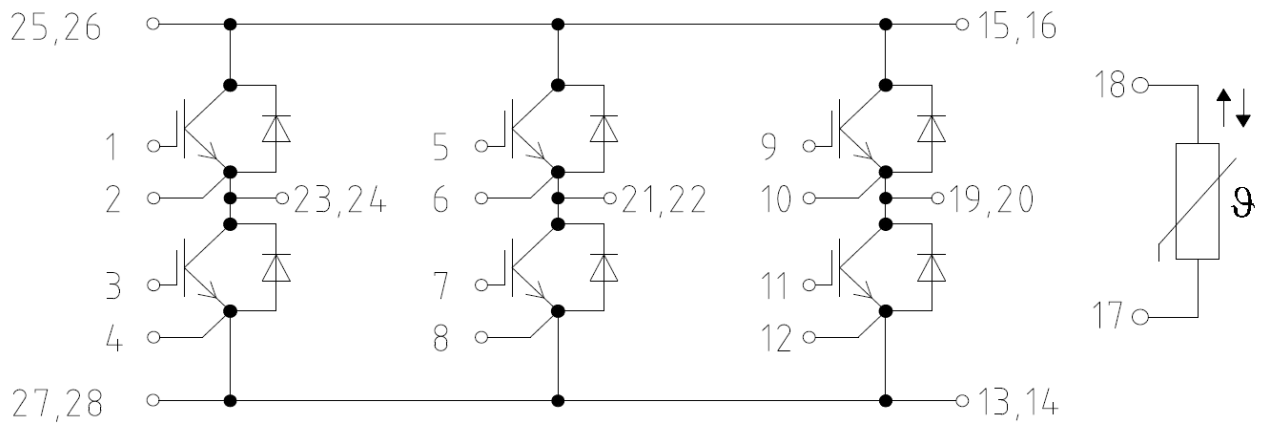
Reverse bias safe operating area IGBT, Inverter (RBSOA)

$I_C = f(V_{CE})$

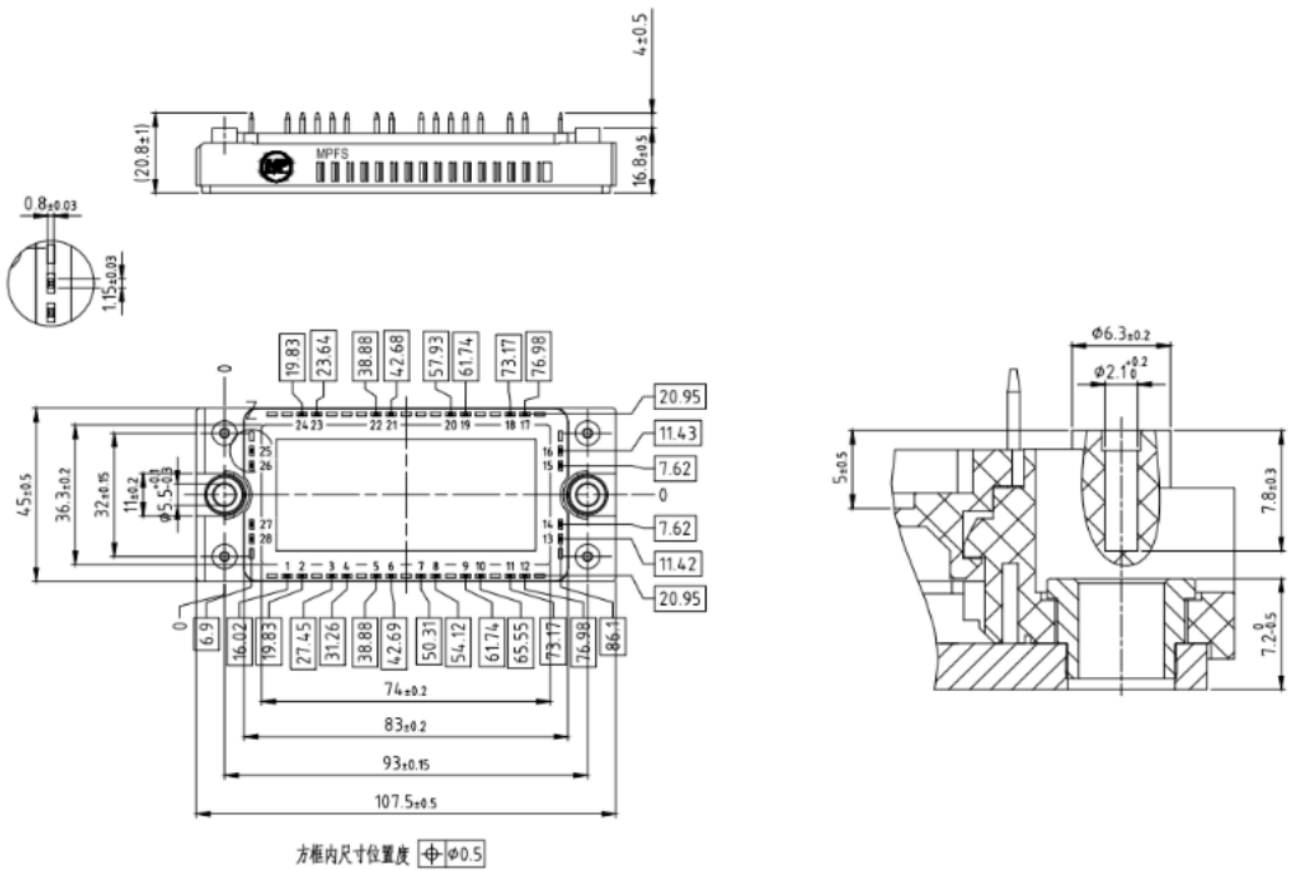
$V_{GE} = \pm 15\text{V}, R_{Goff} = 15\Omega, T_{vj} = 150^\circ\text{C}$



Circuit Diagram



Package Outlines



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序号 Item	日期 Date	变更记录及描述 Change History Description	版本序号 Rev. item	经办人 Responsibility
1	2023.9.23	初版规格书发布，版本为V1.0	2023 9 Ver1.0	梁华文
2	2023.10.30	更新高温数据、短路电流、高温动静态曲线、安全工作曲线、结电容，版本为V1.1	2023 10Ver1.1	张成宇